

Barsha Jain

List of Publications by Year in descending order

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papers

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citations

1039880

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#	ARTICLE	IF	CITATIONS
1	Polarization-Engineered p-Type Electron-Blocking-Layer-Free III-Nitride Deep-Ultraviolet Light-Emitting Diodes for Enhanced Carrier Transport. <i>Journal of Electronic Materials</i> , 2022, 51, 838-846.	1.0	3
2	A novel $\text{In}^2\text{Ga}_2\text{O}_3$ HEMT with f_T of 166 GHz and P_{OUT} of 2.91 W/mm . <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2021, 34, .	1.2	20
3	Improved Performance of Electron Blocking Layer Free AlGaN Deep Ultraviolet Light-Emitting Diodes Using Graded Staircase Barriers. <i>Micromachines</i> , 2021, 12, 334.	1.4	4
4	Controlled carrier mean free path for the enhanced efficiency of III-nitride deep-ultraviolet light-emitting diodes. <i>Applied Optics</i> , 2021, 60, 3088.	0.9	2
5	Effect of HfO ₂ Passivation Layer on Light Extraction Efficiency of AlInN Nanowire Ultraviolet Light-Emitting Diodes. <i>ECS Meeting Abstracts</i> , 2021, MA2021-01, 1073-1073.	0.0	0
6	Effect of HfO ₂ Passivation Layer on Light Extraction Efficiency of AlInN Nanowire Ultraviolet Light-Emitting Diodes. <i>ECS Transactions</i> , 2021, 102, 35-42.	0.3	2
7	Enhancing Efficiency of AlGaN Ultraviolet Light-Emitting Diodes with Graded p-AlGaN Hole Injection Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100003.	0.8	4
8	Improving Color Quality of Nanowire White Light-Emitting Diodes with Mn ⁴⁺ Doped Fluoride Nanosheets. <i>Micromachines</i> , 2021, 12, 965.	1.4	5
9	Epitaxial Growth and Characterization of AlInN-Based Core-Shell Nanowire Light Emitting Diodes Operating in the Ultraviolet Spectrum. <i>Scientific Reports</i> , 2020, 10, 2547.	1.6	23
10	Improving carrier transport in AlGaN deep-ultraviolet light-emitting diodes using a strip-in-a-barrier structure. <i>Applied Optics</i> , 2020, 59, 5276.	0.9	20
11	Enhanced hole transport in AlGaN deep ultraviolet light-emitting diodes using a double-sided step graded superlattice electron blocking layer. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2020, 37, 2564.	0.9	9
12	High performance electron blocking layer-free InGaN/GaN nanowire white-light-emitting diodes. <i>Optics Express</i> , 2020, 28, 665.	1.7	35
13	Enhancing the light extraction efficiency of AlInN nanowire ultraviolet light-emitting diodes with photonic crystal structures. <i>Optics Express</i> , 2020, 28, 22908.	1.7	14
14	High-performance electron-blocking-layer-free deep ultraviolet light-emitting diodes implementing a strip-in-a-barrier structure. <i>Optics Letters</i> , 2020, 45, 5125.	1.7	11
15	Numerical investigation on the device performance of electron blocking layer free AlInN nanowire deep ultraviolet light-emitting diodes. <i>Optical Materials Express</i> , 2020, 10, 472.	1.6	12
16	III-Nitride Based Narrow Band Far-UVC LEDs for Airborne and Surface Disinfection. <i>ECS Transactions</i> , 2020, 98, 83-89.	0.3	0
17	Single and double-gate based AlGaIn/GaN MOS-HEMTs for the design of low-noise amplifiers: a comparative study. <i>IET Circuits, Devices and Systems</i> , 2020, 14, 1018-1025.	0.9	11
18	Electron Blocking Layer Free Full-Color InGaIn/GaN White Light-Emitting Diodes. <i>ECS Meeting Abstracts</i> , 2020, MA2020-02, 2743-2743.	0.0	1

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19	III-Nitride Based Narrow Band Far-UVC LEDs for Airborne and Surface Disinfection. ECS Meeting Abstracts, 2020, MA2020-02, 1825-1825.	0.0	0
20	Ultraviolet Light-Emitting Diodes Using Aluminium Indium Nitride Nanowire Structures. ECS Meeting Abstracts, 2020, MA2020-02, 2739-2739.	0.0	0
21	Full-Color InGaN/AlGaIn Nanowire Micro Light-Emitting Diodes Grown by Molecular Beam Epitaxy: A Promising Candidate for Next Generation Micro Displays. Micromachines, 2019, 10, 492.	1.4	51
22	Multilevel Resistive Switching in Hf-Based RRAM. ECS Transactions, 2019, 89, 39-44.	0.3	10
23	Bilayer Dielectrics for RRAM Devices. ECS Transactions, 2018, 86, 77-83.	0.3	3
24	A tetracene-based single-electron transistor as a chlorine sensor. Journal of Computational Electronics, 2018, 17, 1515-1520.	1.3	5
25	High-efficiency InGaN blue LEDs with reduced positive sheet polarization. Applied Optics, 0, , .	0.9	2